

KTD1624 (3DG1624)

硅 NPN 半导体三极管/SILICON NPN TRANSISTOR

用途:用于电压调整器, 转播驱动器, 灯管驱动器, 电力设备。

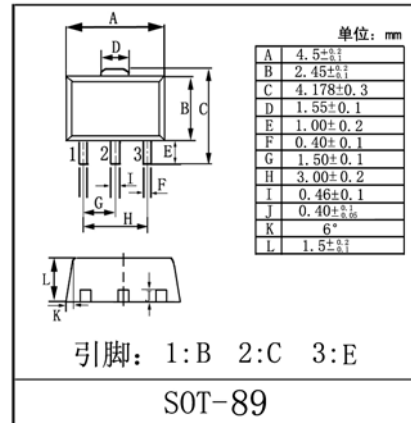
Purpose: Voltage regulators ,relay drivers lamp drivers, electrical equipment.

特点: 选用 MBIT 工艺规程, 集电极-发射极饱和压降低, 开关速度快, 小电流电容和宽阔的安全工作区, 可与互补 KTB1124 (3CG1124)。

Features: Adoption of MBIT processes, low collector-to-emitter saturation voltage, fast Switching Speed, Large current capacity and wide ASO, Complementary to KTB1124 (3CG1124).

极限参数/Absolute maximum ratings (Ta=25°C)

参数符号 Symbol	数值 Rating	单位 Unit
V _{CBO}	60	V
V _{CEO}	50	V
V _{EBO}	6.0	V
I _C	3.0	A
I _{CP}	6.0	A
P _C (Ta=25°C)	500	mW
P _C (Ta=25°C)*	1	W
T _J	150	°C
T _{stg}	-55~150	°C



*:Package mounted on ceramic substrate(250mm²×0.8t)

电性能参数/Electrical characteristics (Ta=25°C)

参数符号 Symbol	测试条件 Test condition	数值 Rating			单位 Unit
		最小值 Min	典型值 Typ	最大值 Max	
V _{CBO}	I _C =10 μ A I _E =0	60			V
V _{CEO}	I _C =1.0mA I _B =0	50			V
V _{EBO}	I _E =10 μ A I _C =0	6.0			V
I _{CBO}	V _{CB} =40V I _E =0			1.0	μ A
I _{EBO}	V _{EB} =4.0V I _C =0			1.0	μ A
h _{FE(1)}	V _{CE} =2.0V I _C =100mA	100		400	
h _{FE(2)}	V _{CE} =2.0V I _C =3.0A	35			
V _{CE(sat)}	I _C =2.0A I _B =100mA		0.19	0.5	V
V _{BE(sat)}	I _C =2.0A I _B =100mA		0.94	1.2	V
f _T	V _{CE} =10V I _C =50mA		150		MHz
C _{ob}	V _{CB} =10V I _E =0 f=1MHz		25		pF
t _{on}	10I _{B1} =-10I _{B2} =I _C =1.0A		70		nS
t _{stg}			650		nS
t _f			35		nS

h_{FE(1)} 分档、印章标记/h_{FE(1)} Classifications、Marking:

h _{FE(1)} 分档 h _{FE(1)} Classifications	A	B	C
h _{FE(1)} 范围 h _{FE(1)} Range	100~200	140~280	200~400
印章 Marking	YHA * *	YHB * *	YHC * *

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